

SEMICONDUCTOR DEVICE HAVING JUNCTION DIODE AND  
FABRICATING METHOD THEREFOR

RELATED APPLICATION

5        This application is a divisional of U.S. application serial number 09/645,285, filed  
         *now Patent No. 6,717,209*  
         on August 24, 2000, which relies for priority upon Korean Patent Application No. 99-  
         42805, filed on October 5, 1999, the contents of which are herein incorporated by reference  
         in their entirety.

10      BACKGROUND OF THE INVENTION  
         FIELD OF THE INVENTION

         The present invention relates to a semiconductor device and a fabricating method  
         therefor, and more particularly to a semiconductor device having a junction diode and a  
         fabricating method therefor wherein the junction diode is configured for preventing a gate  
15      insulating layer from deterioration arising from a plasma etch process necessary for device  
         wire layout.

DESCRIPTION OF THE PRIOR ART

         As ULSI semiconductor technology advances, there is an ever-increasing demand  
20      for high integration, fine wire and gate patterns, high performance, and wafers of large  
         diameter and high yield. For this reason, the plasma process has become an indispensable  
         technology in the field of semiconductor device fabrication.

         Representative examples of plasma processes include the well-known processes of  
         dry etching, thin layer deposition with plasma CVD, ashing, blanket etch-back and the like.